








Types covered by similarity: Variant 01 in each Detail Specification is qualified.				Remarks: These devices have a TID tested capability of 100 kRad (Si) SEE tested : LET (MeV-cm ² /mg) 56 @ V _{GS} = -10V, V _{DS} = 250V SOA and SE SOA derating graphs are incorporated in the Detail Specifications.			
Procurement Specifications		Manufacturer		Nature of Approval	Supervising Authority	Date	
Generic ESCC 5000 Detail ESCC 5205/026 5205/027 5205/028		Infineon Technologies AG Neubiberg Germany		Qualification	DLR	Aug 2012	
Characteristics: ESCC No.		5205/026	5205/027	5205/028			
r _{DS(ON)} (mΩ) @ 25 °C		130	30	130			
Maximum Ratings:							
I _{DS} (A)		12.4	54	12.4			
V _{DS} (V) max.		250	250	100			
V _{GS} (V) max.		± 20	± 20	± 20			
P _{tot} (W)		75	250	75			
R _{th(j-c)} (°C/W)		1.66	0.5	1.66			
Package:		SMD0.5	SMD2	SMD0.5			
Operating Temperature Range (°C): T _{op} = - 55 to +150							
 		TRANSISTORS, POWER, MOSFET, N-CHANNEL, BASED ON TYPE BUY **CS***			Current validity of Qualification		Page
					Certificate	Valid Until	12-05
					319	August 2014	003-2


Types covered by similarity: Variants 01 to 08 are qualified.		Remarks:																										
Procurement Specifications		Manufacturer	Nature of Approval	Supervising Authority	Date																							
Generic ESCC 5010		Infineon Technologies AG Neubiberg Germany	Qualification	DARA	Jun 1996																							
Detail ESCC 5611/006			Extension	DLR	Jan 2000																							
<p>Characteristics for BFY 193</p> <table border="0"> <tr> <td>V_{CE0} (V) max.</td> <td></td> <td>12</td> <td></td> </tr> <tr> <td>V_{CBO} (V) max.</td> <td></td> <td>20</td> <td></td> </tr> <tr> <td>h_{FE} min/max.</td> <td></td> <td>50/175</td> <td>@ $V_{CE} = 8.0$ V, $I_C = 30$ mA</td> </tr> <tr> <td>NF (dB) max.</td> <td>@ 2 GHz</td> <td>2.9</td> <td>@ $V_{CE} = 5.0$ V, $I_C = 15$ mA</td> </tr> <tr> <td>MAG/MSG (dB) min.</td> <td>@ 2 GHz</td> <td>12.5</td> <td>@ $V_{CE} = 5.0$ V, $I_C = 40$ mA</td> </tr> <tr> <td>f_T (GHz) min.</td> <td>@ 500 MHz</td> <td>6.5</td> <td>@ $V_{CE} = 5.0$ V, $I_C = 40$ mA</td> </tr> </table> <p>Package: " Micro-X1"</p> <p>Total Power Dissipation (P_{tot}) = 580 mW</p> <p>Operating Temperature Range (°C): $T_{op} = - 65$ to +200</p>		V_{CE0} (V) max.		12		V_{CBO} (V) max.		20		h_{FE} min/max.		50/175	@ $V_{CE} = 8.0$ V, $I_C = 30$ mA	NF (dB) max.	@ 2 GHz	2.9	@ $V_{CE} = 5.0$ V, $I_C = 15$ mA	MAG/MSG (dB) min.	@ 2 GHz	12.5	@ $V_{CE} = 5.0$ V, $I_C = 40$ mA	f_T (GHz) min.	@ 500 MHz	6.5	@ $V_{CE} = 5.0$ V, $I_C = 40$ mA	Extension	DLR	Nov 2004
		V_{CE0} (V) max.		12																								
		V_{CBO} (V) max.		20																								
		h_{FE} min/max.		50/175	@ $V_{CE} = 8.0$ V, $I_C = 30$ mA																							
		NF (dB) max.	@ 2 GHz	2.9	@ $V_{CE} = 5.0$ V, $I_C = 15$ mA																							
MAG/MSG (dB) min.	@ 2 GHz	12.5	@ $V_{CE} = 5.0$ V, $I_C = 40$ mA																									
f_T (GHz) min.	@ 500 MHz	6.5	@ $V_{CE} = 5.0$ V, $I_C = 40$ mA																									
Requalification	DLR	Mar 2008																										
Requalification	DLR	Nov 2010																										
Extension	DLR	Mar 2012																										
 <p style="text-align: center;">TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPE BFY 193</p>		Current validity of Qualification		Page																								
		Certificate	Valid Until	12-10																								
		230 E	March 2014	001																								

Types covered by similarity: Variants 01, 02 and 03 are qualified.			Remarks:		
Procurement Specifications		Manufacturer	Nature of Approval	Supervising Authority	Date
Generic ESCC 5010		Infineon Technologies AG Neubiberg Germany	Qualification	DARA	Jun 1997
Detail ESCC 5611/008			Extension	DLR	Jan 2000
Characteristics for BFY 450 V_{CE0} (V) max. 4.5 V_{CBO} (V) max. 15 I_C (mA) max. 100 I_B (mA) max. 10 h_{FE} min/max. 50/150 @ $V_{CE} = 1.0$ V, $I_C = 20$ mA NF (dB) max. @ 1.8 GHz 2.0 @ $V_{CE} = 2.0$ V, $I_C = 10$ mA f_T (GHz) min. @ 1.0 GHz 18 @ $V_{CE} = 3.0$ V, $I_C = 90$ mA Package: "Micro-X" Total Power Dissipation (P_{tot}) = 450 mW Operating Temperature Range (°C): $T_{op} = - 65$ to +175			Extension	DLR	Dec 2003
			Requalification	DLR	Mar 2008
			Requalification	DLR	Nov 2010
			Extension	DLR	Mar 2012
					

Types covered by similarity: Variants 01, 02 and 03 are qualified.		Remarks: -																														
Procurement Specifications		Manufacturer	Nature of Approval	Supervising Authority	Date																											
Generic ESCC 5010 Detail ESCC 5611/009		Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Sep 2012																											
Characteristics for BFY 640 Variant 03 <table border="0"> <tr> <td>V_{CE0} (V) max.</td> <td></td> <td>4.0</td> </tr> <tr> <td>V_{CB0} (V) max.</td> <td></td> <td>13</td> </tr> <tr> <td>I_C (mA) max.</td> <td></td> <td>50.0</td> </tr> <tr> <td>I_B (mA) max.</td> <td></td> <td>3.0</td> </tr> <tr> <td>h_{FE} min/max</td> <td></td> <td>135/250 @ V_{ce}=3V & I_C=30mA</td> </tr> <tr> <td>MSG/MAG min (dB)</td> <td>@ 1.8GHz</td> <td>23 @ V_{ce}=3V & I_C= 30mA</td> </tr> <tr> <td></td> <td>@ 6.0 GHz</td> <td>12 V_{ce}=3V & I_C= 30mA</td> </tr> <tr> <td>NF_{max} (dB)</td> <td>@ 1.8 GHz</td> <td>< 0.8 @ V_{ce}=3V & I_C=5mA</td> </tr> <tr> <td>NF_{max} (dB)</td> <td>@ 6.0 GHz</td> <td>< 1.4 @ V_{ce}=3V & I_C=5mA</td> </tr> </table> Package: "Micro-X" Total Power Dissipation (P _{tot}) max. = 200 mW Operating Temperature Range (°C): T _{op} = - 65 to +175		V _{CE0} (V) max.		4.0	V _{CB0} (V) max.		13	I _C (mA) max.		50.0	I _B (mA) max.		3.0	h _{FE} min/max		135/250 @ V _{ce} =3V & I _C =30mA	MSG/MAG min (dB)	@ 1.8GHz	23 @ V _{ce} =3V & I _C = 30mA		@ 6.0 GHz	12 V _{ce} =3V & I _C = 30mA	NF _{max} (dB)	@ 1.8 GHz	< 0.8 @ V _{ce} =3V & I _C =5mA	NF _{max} (dB)	@ 6.0 GHz	< 1.4 @ V _{ce} =3V & I _C =5mA				
V _{CE0} (V) max.		4.0																														
V _{CB0} (V) max.		13																														
I _C (mA) max.		50.0																														
I _B (mA) max.		3.0																														
h _{FE} min/max		135/250 @ V _{ce} =3V & I _C =30mA																														
MSG/MAG min (dB)	@ 1.8GHz	23 @ V _{ce} =3V & I _C = 30mA																														
	@ 6.0 GHz	12 V _{ce} =3V & I _C = 30mA																														
NF _{max} (dB)	@ 1.8 GHz	< 0.8 @ V _{ce} =3V & I _C =5mA																														
NF _{max} (dB)	@ 6.0 GHz	< 1.4 @ V _{ce} =3V & I _C =5mA																														
	TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPE BFY 640		Current validity of Qualification		Page																											
			Certificate	Valid Until	12-10																											
			320	September 2014	003																											

Types covered by similarity: Variants 01, 02, 03 and 04 are qualified.		Remarks:																							
Procurement Specifications		Manufacturer	Nature of Approval	Supervising Authority	Date																				
Generic ESCC 5010 Detail ESCC 5611/010		Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Sep 2012																				
<p>Characteristics for BFY 650B Variant 04</p> <table border="0"> <tr> <td>V_{CEO} (V) max.</td> <td></td> <td>4.0</td> </tr> <tr> <td>V_{CBO} (V) max.</td> <td></td> <td>13</td> </tr> <tr> <td>I_C (mA) max.</td> <td></td> <td>150</td> </tr> <tr> <td>I_B (mA) max.</td> <td></td> <td>10</td> </tr> <tr> <td>h_{FE} min/max</td> <td></td> <td>100/250 @ V_{CE}=3V & I_C=80mA</td> </tr> <tr> <td>MSG/MAG min (dB)</td> <td>@1.8 GHz</td> <td>18 @ V_{CE}=3V & I_C=80mA</td> </tr> <tr> <td>P_{out} (dBm)</td> <td>@ 1.8 GHz</td> <td>16</td> </tr> </table> <p>Package: "Micro-X"</p> <p>Total Power Dissipation (P_{tot}) max. = 600 mW</p> <p>Operating Temperature Range (°C): T_{op} = - 65 to +175</p>		V _{CEO} (V) max.		4.0	V _{CBO} (V) max.		13	I _C (mA) max.		150	I _B (mA) max.		10	h _{FE} min/max		100/250 @ V _{CE} =3V & I _C =80mA	MSG/MAG min (dB)	@1.8 GHz	18 @ V _{CE} =3V & I _C =80mA	P _{out} (dBm)	@ 1.8 GHz	16			
V _{CEO} (V) max.		4.0																							
V _{CBO} (V) max.		13																							
I _C (mA) max.		150																							
I _B (mA) max.		10																							
h _{FE} min/max		100/250 @ V _{CE} =3V & I _C =80mA																							
MSG/MAG min (dB)	@1.8 GHz	18 @ V _{CE} =3V & I _C =80mA																							
P _{out} (dBm)	@ 1.8 GHz	16																							
		<p>TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPES BFY 640B and BFY650B</p>		Current validity of Qualification		Page																			
				Certificate	Valid Until	12-10																			
				321	September 2014	004																			

Types covered by similarity:		Remarks:																														
Procurement Specifications		Manufacturer	Nature of Approval	Supervising Authority	Date																											
Generic ESCC 5010 Detail ESCC 5611/011		Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Sep 2012																											
Characteristics for BFY 740B Variant 01 <table border="0"> <tr> <td>V_{CEO} (V) max.</td> <td></td> <td>4.0</td> </tr> <tr> <td>V_{CBO} (V) max.</td> <td></td> <td>13</td> </tr> <tr> <td>I_C (mA) max.</td> <td></td> <td>30.0</td> </tr> <tr> <td>I_B (mA) max.</td> <td></td> <td>3.0</td> </tr> <tr> <td>h_{FE} min/max</td> <td></td> <td>185/380 @V_{CE}=3V & I_C=20mA</td> </tr> <tr> <td>MSG/MAG min (dB)</td> <td>@ 1.8 GHz</td> <td>24 @V_{CE}=3V & I_C=20mA</td> </tr> <tr> <td>MSG/MAG min (dB)</td> <td>@ 6.0 GHz</td> <td>17 @V_{CE}=3V & I_C=20mA</td> </tr> <tr> <td>NF_{max} (dB)</td> <td>@ 1.8 GHz</td> <td>≤ 0.75 @V_{CE}=3V & I_C=8mA</td> </tr> <tr> <td>NF_{max} (dB)</td> <td>@ 6.0 GHz</td> <td>≤ 1.15 @V_{CE}=3V & I_C=8mA</td> </tr> </table> Package: "Micro-X" Total Power Dissipation (P _{tot}) max. = 120 mW Operating Temperature Range (°C): T _{op} = - 65 to +175		V _{CEO} (V) max.		4.0	V _{CBO} (V) max.		13	I _C (mA) max.		30.0	I _B (mA) max.		3.0	h _{FE} min/max		185/380 @V _{CE} =3V & I _C =20mA	MSG/MAG min (dB)	@ 1.8 GHz	24 @V _{CE} =3V & I _C =20mA	MSG/MAG min (dB)	@ 6.0 GHz	17 @V _{CE} =3V & I _C =20mA	NF _{max} (dB)	@ 1.8 GHz	≤ 0.75 @V _{CE} =3V & I _C =8mA	NF _{max} (dB)	@ 6.0 GHz	≤ 1.15 @V _{CE} =3V & I _C =8mA				
V _{CEO} (V) max.		4.0																														
V _{CBO} (V) max.		13																														
I _C (mA) max.		30.0																														
I _B (mA) max.		3.0																														
h _{FE} min/max		185/380 @V _{CE} =3V & I _C =20mA																														
MSG/MAG min (dB)	@ 1.8 GHz	24 @V _{CE} =3V & I _C =20mA																														
MSG/MAG min (dB)	@ 6.0 GHz	17 @V _{CE} =3V & I _C =20mA																														
NF _{max} (dB)	@ 1.8 GHz	≤ 0.75 @V _{CE} =3V & I _C =8mA																														
NF _{max} (dB)	@ 6.0 GHz	≤ 1.15 @V _{CE} =3V & I _C =8mA																														
	TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPE BFY 740B		Current validity of Qualification		Page																											
			Certificate	Valid Until	12-10																											
			322	September 2014	005																											

Types covered by similarity:				Remarks:											
Procurement Specifications		Manufacturer		Nature of Approval	Supervising Authority	Date									
Generic ESCC 5010		Infineon Technologies AG Neubiberg Germany		Qualification	DARA	Apr 1994									
Detail ESCC 5613/004				Extension	DLR	Jan 2000									
Characteristics (@ 12 GHz): All variants are qualified				Extension	DLR	Dec 2003									
				Requalification	DLR	Mar 2008									
		<table border="1"> <thead> <tr> <th></th> <th>NFmin. (dB)</th> <th>Ga (dB)</th> </tr> </thead> <tbody> <tr> <td>5613/004</td> <td>0.8</td> <td>11</td> </tr> <tr> <td>pseudo-morphic</td> <td>1.0</td> <td>10.5</td> </tr> </tbody> </table>			NFmin. (dB)	Ga (dB)	5613/004	0.8	11	pseudo-morphic	1.0	10.5	Requalification	DLR	Nov 2010
	NFmin. (dB)	Ga (dB)													
5613/004	0.8	11													
pseudo-morphic	1.0	10.5													
				Extension	DLR	Mar 2012									
Package: Micro-X Total Power Dissipation (P_{tot}) = 200 mW derated from $+31\text{ }^{\circ}\text{C } T_{amb}$ Operating Temperature Range ($^{\circ}\text{C}$): $T_{stg} = -65$ to $+150$															
		TRANSISTORS, HIGH ELECTRON MOBILITY, GALLIUM ARSENIDE, MICROWAVE, LOW NOISE, SMALL SIGNAL, BASED ON TYPE CFY 67			Current validity of Qualification		Page								
					Certificate	Valid Until	12-16								
				213 E	March 2014	001									